



Schottky Barrier Diode

Qualified per MIL-PRF-19500/444

Qualified Levels: JAN, JANTX, and JANTXV

DESCRIPTION

This Schottky barrier diode is metallurgically bonded and offers military grade qualifications for high-reliability applications on "1N" prefixed numbers. This small diode is hermetically sealed and bonded into a DO-35 glass package.

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FEATURES

- JEDEC registered 1N5711-1, 1N5712-1, 1N6857-1, and 1N6858-1 numbers.
- Metallurgically bonded.
- JAN, JANTX, JANTXV and commercial qualifications also available per MIL-PRF-19500/444 on "1N" numbers only.

(See Part Nomenclature for all available options).

RoHS compliant versions available (commercial grade only).

APPLICATIONS / BENEFITS

- Low reverse leakage characteristics.
- Small size for high density mounting using flexible thru-hole leads (see package illustration).
- ESD sensitive to Class 1.

DO-213AA package

(surface mount) 1N5711UR-1, 1N5712UR-1, 1N6857UR-1, and 1N6858UR-1

DO-35 (DO-204AH)

Also available in:

📆 UB package

(3-pin surface mount)
1N5711UB, 1N5712UB

Package

(B, CC, CA)

MAXIMUM RATINGS @ 25 °C unless otherwise stated

| Parameters/Test Conditions | Symbol | Value | Unit |
|--|---------------------|-------------|------|
| Junction and Storage Temperature | T_J and T_{STG} | -65 to +150 | °C |
| Thermal Resistance, Junction-to-Lead | $R_{\Theta JL}$ | 250 | °C/W |
| @ lead length = 0.375 inch (9.52 mm) from body | | | |
| Average Rectified Output Current: | | | |
| 1N5711 ⁽¹⁾ | Io | 33 | mA |
| DSB2810, DSB5712, 1N5712 & 1N6858 (2) | | 75 | |
| 1N6857 ⁽³⁾ | | 150 | |
| Solder Temperature @ 10 s | | 260 | °C |

NOTES: 1. At $T_L = +130$ °C and L = 0.375 inch, derate I_O to 0 at +150°C.

2. At T_L = +110°C and L = 0.375 inch, derate I_O to 0 at +150°C.

3. At $T_L = +70$ °C and L = 0.375 inch, derate I_O to 0 at +150°C.

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MECHANICAL and PACKAGING

- CASE: Hermetically sealed glass package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode indicated by band.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: Approximately 0.2 grams.
- See Package Dimensions on last page.

PART NOMENCLATURE **JAN** 1N5711 -1 (e3)**Reliability Level** RoHS Compliance JAN = JAN level e3 = RoHS compliant (on JANTX = JANTX level commercial grade only) JANTXV = JANTXV level Blank = non-RoHS compliant CDS (reference JANS)* Blank = Commercial grade Metallurgically Bonded *Available only on 1N5711-1 JEDEC type number (see Electrical Characteristics table) **DSB** 2810 (e3)**Diode Schottky Barrier RoHS Compliance** e3 = RoHS compliant Series number Blank = non-RoHS compliant

| SYMBOLS & DEFINITIONS | | | | |
|-----------------------|---|--|--|--|
| Symbol | Definition | | | |
| С | Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage. | | | |
| f | frequency | | | |
| I_R | Reverse Current: The dc current flowing from the external circuit into the cathode terminal at the specified voltage V _R . | | | |
| Io | Average Rectified Output Current: The Output Current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle. | | | |
| t _{rr} | Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs. | | | |
| V _(BR) | Breakdown Voltage: A voltage in the breakdown region. | | | |
| V _F | Forward Voltage: A positive dc anode-cathode voltage the device will exhibit at a specified forward current. | | | |
| V _R | Reverse Voltage: A positive dc cathode-anode voltage below the breakdown region. | | | |
| V _{RWM} | Working Peak Reverse Voltage: The peak voltage excluding all transient voltages (ref JESD282-B). Also sometimes known historically as PIV. | | | |

(see Electrical Characteristics

table)



ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

| TYPE NUMBER | MINIMUM BREAKDOWN VOLTAGE | MAXIMUM FORWARD VOLTAGE | MAXIMUM FORWARD VOLTAGE | WORKING PEAK REVERSE VOLTAGE | MAXIMUM REVERSE LEAKAGE CURRENT | | MAXIMUM CAPACITANCE @ V _R = 0 VOLTS f = 1.0 MHz |
|----------------|---------------------------------|-------------------------------|---------------------------------|---------------------------------------|--|------------------|--|
| | V _(BR) @ 10 μA | V _F @ 1 mA | V _F @ I _F | V _{RWM} | I _R (| 2 V _R | С |
| | Volts | Volts | V @ mA | V (pk) | nA | Volts | pF |
| 1N5711-1 | 70 | 0.41 | 1.0 @ 15 | 50 | 200 | 50 | 2.0 |
| 1N5712-1 | 20 | 0.41 | 1.0 @ 35 | 16 | 150 | 16 | 2.0 |
| 1N6857-1 | 20 | 0.35 | 0.75 @ 35 | 16 | 150 | 16 | 4.5 |
| 1N6858-1 | 70 | 0.36 | 0.65 @ 15 | 50 | 200 | 50 | 4.5 |
| DSB2810 | 20 | 0.41 | 1.0 @ 35 | 16 | 100 | 15 | 2.0 |
| DSB5712 | 20 | 0.41 | 1.0 @ 35 | 16 | 150 | 16 | 2.0 |



GRAPHS

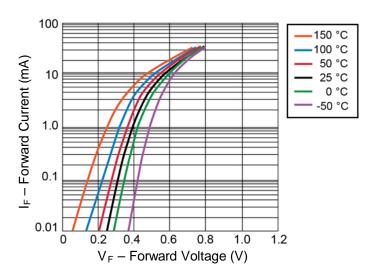


FIGURE 1

<u>I-V Curve showing typical Forward Voltage Variation</u>

Temperature for the 1N5712-1, DSB5712 and DSB2810 Schottky Diodes

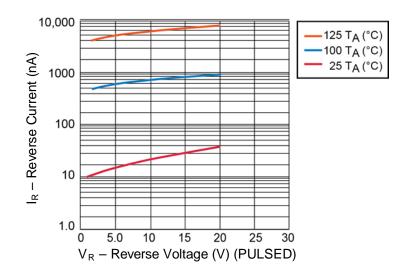


FIGURE 2 1N5712-1, DSB5712 and DSB2810 Typical variation of Reverse Current (I_R) vs Reverse Voltage (V_R) at Various Temperatures



GRAPHS

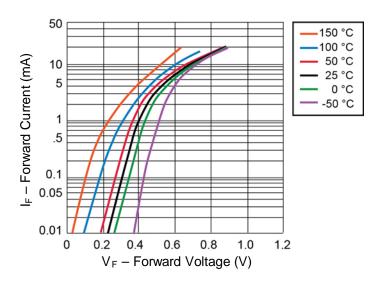


FIGURE 3

I – V curve showing typical Forward Voltage Variation
With Temperature Schottky Diode 1N5711

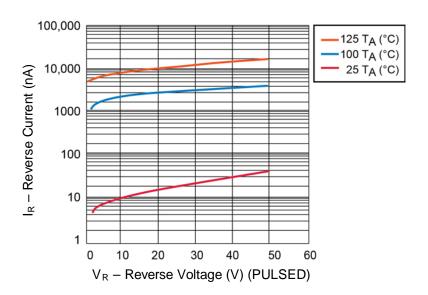


FIGURE 4

1N5711 Typical Variation of Reverse Current (I_R) vs Reverse Voltage (V_R)

at Various Temperatures



GRAPHS

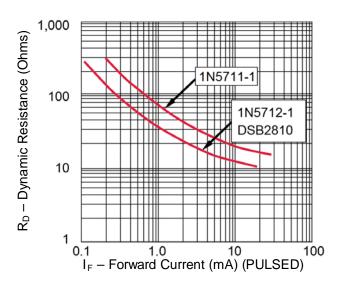
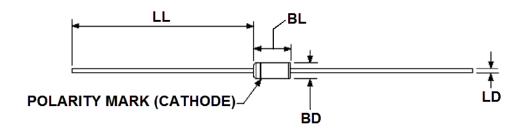


FIGURE 5 Typical Dynamic Resistance (R_D) vs Forward Current (I_F)



PACKAGE DIMENSIONS



NOTES:

- 1. Dimensions are in inches. Millimeters are given for information only.
- 2. Dimensions BL and LD includes all components of the diode periphery expect the section of the leads over which the diameter is controlled.
- 3. Dimension BD shall be measured at the largest diameter.
- 4. In accordance with ASME Y1.4M, diameters are equivalents to φx symbology.

| | Dimensions | | | | |
|--------|------------|-------|-------------|-------|-------|
| Symbol | Inches | | Millimeters | | Notes |
| | Min | Max | Min | Max | |
| BD | 0.068 | 0.076 | 1.73 | 1.93 | 2,3 |
| BL | 0.125 | 0.170 | 3.18 | 4.32 | 2 |
| LD | 0.014 | 0.022 | 0.36 | 0.56 | |
| LL | 1.000 | 1.500 | 25.40 | 38.10 | |

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<u>1N5712 1N5712-1 1N6857-1 1N6858UR-1 1N6858-1 1N6857UR-1 CDLL2810/TR JANTX1N5712-1/TR 1N6858-1 1/TR JANTXV1N5711-1/TR JAN1N5712-1/TR CDLL2810e3/TR CDLL2810e3 JAN1N5711-1/TR 1N6857-1/TR 1N5712/TR 1N5712-1/TR 1N5712-1/TR 1N5711-1/TR 1N5711-1/TR</u>